PNP Epitaxial Planar Silicon Transistor



2SB1205

Strobe High-Current Switching Applications

Applications

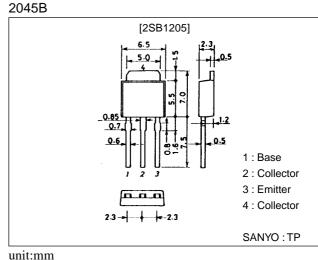
• Strobe, voltage regulators, relay drivers, lamp drivers.

Features

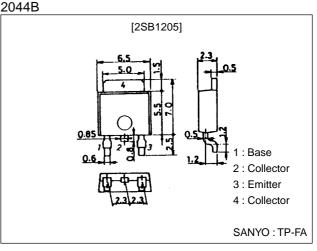
- · Adoption of FBET, MBIT processes.
- \cdot Low saturation voltage.
- · Fast switching speed.
- · Large current capacity.
- Small and slim package making it easy to make 2SB1205-applied sets smaller.

Package Dimensions

unit:mm



00445



- Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.
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Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

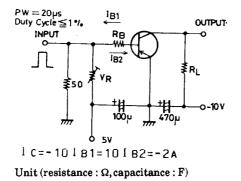
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		-25	V
Collector-to-Emitter Voltage	VCEO		-20	V
Emitter-to-Base Voltage	VEBO		-5	V
Collector Current	۱ _C		-5	A
Collector Current (Pulse)	ICP		-8	A
Base Current	IB		-0.5	A
Collector Dissipation	PC		1	W
		Tc=25°C	10	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

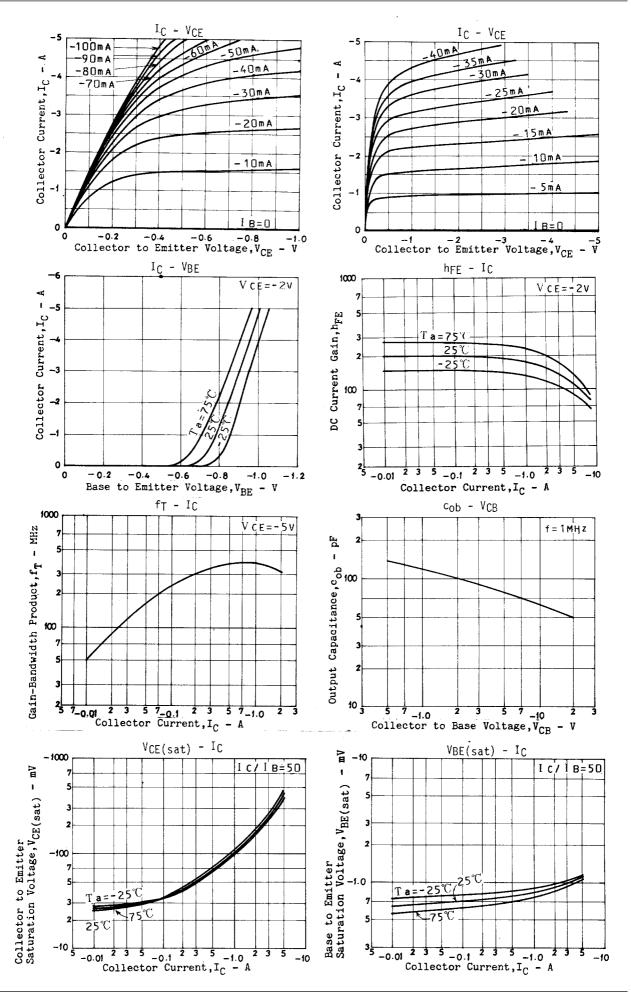
Electrical Characteristics at Ta = 25°C

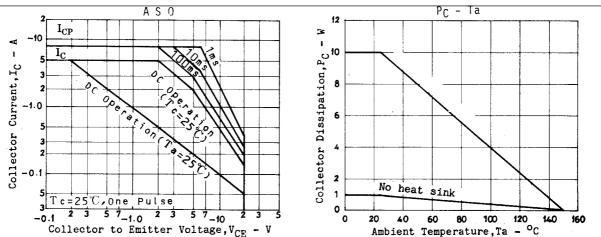
Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =-20V, I _E =0			-500	nA
Emitter Cutoff Current	IEBO	V _{EB} =-4V, I _C =0			-500	nA
DC Current Gain	h _{FE} 1	V _{CE} =-2V, I _C =500mA	100*		400*	
	h _{FE} 2	V _{CE} =-2V, I _C =-4A	60			
Gain-Bandwidth Product	fT	V _{CE} =-5V, I _C =-200mA		320		MHz
Output Capacitance	Cob	V _{CE} =-10V, f=1MHz		60		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-3A, I _B =-60mA		-250	-500	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-3A, I _B =-60mA		-1.0	-1.3	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =-10µA, I _E =0	-25			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =−1mA, R _{BE} =∞	-20			V
Emitter-to-Base Breakdown Voltage	V _{(BE)EBO}	I _E =-10μA, I _C =0	-5			V
Turn-ON Time	ton	See specified Test Circuit		40		ns
Storage Time	tstg	See specified Test Circuit		200		ns
Fall Time	tf	See specified Test Circuit		10		ns

 \ast : The 2SB1205 is classified by 500mA $h_{_{\rm FE}}$ as follows :

Switching Time Test Circuit







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